Vishay Semiconductors

Phase Control Thyristors (Hockey PUK Version), 1473 A



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PRODUCT SUMMARY					
Package	A-24 (K-PUK)				
Diode variation	Single SCR				
I _{T(AV)}	1473 A				
V _{DRM} /V _{RRM}	1200 V, 1600 V, 1800 V, 2000 V, 2200 V, 2400 V, 2600 V				
V _{TM}	1.80 V				
I _{GT}	100 mA				
TJ	-40 °C to 125 °C				

FEATURES

- Center amplifying gate
- Metal case with ceramic insulator
- International standard case A-24 (K-PUK)
- High profile hockey PUK
- Material categorization: For definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- DC motor controls
- Controlled DC power supplies
- AC controllers

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES	UNITS			
1		1473	A			
I _{T(AV)}	T _{hs}	55	O°			
1		2913	А			
I _{T(RMS)}	T _{hs}	25	O°			
	50 Hz	20.0	0			
ITSM	60 Hz	21.2	А			
l ² t	50 Hz	2000	kA ² s			
1-1	60 Hz	1865	KA-S			
l²√t		20 000	kA²√s			
V _{DRM} /V _{RRM}	Range	1200 to 2600	V			
t _q	Typical	300	μs			
TJ	Range	-40 to 125	O°			

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	BEVERSE VOLTAGE		I _{RRM} MAXIMUM AT T _J = 125 °C mA			
	12	1200	1300				
	16	1600	1700				
	18	1800	1900				
VS-ST1000CK	20	2000	2100	100			
	22	2200	2300				
	24	2400	2500				
	26	2600	2700				

RoHS COMPLIANT

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ABSOLUTE MAXIMUM RATINGS	5					
PARAMETER	SYMBOL	TEST CONDITIONS			VALUES	UNITS
Maximum average on-state current	I -rece	180° condu	ction, half sine	wave	1473 (630)	А
at heatsink temperature	I _{T(AV)}	Double side	e (single side) co	ooled	55 (85)	°C
Maximum RMS on-state current	I _{T(RMS)}	DC at 25 °C	heatsink temp	erature double side cooled	6540	А
		t = 10 ms	No voltage		20.0	
Maximum peak, one-cycle,	here a	t = 8.3 ms	reapplied		21.2	kA kA kA ² s
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}	Sinusoidal half wave, initial T _J = T _J maximum	17.0	
		t = 8.3 ms	reapplied		18.1	
	l ² t	t = 10 ms	No voltage		2000	
Maximum 12t fax fusing		t = 8.3 ms	reapplied		1865	
Maximum I ² t for fusing		t = 10 ms	100 % V _{RRM}		1445	
		t = 8.3 ms	reapplied		1360	
Maximum I ² \sqrt{t} for fusing	l²√t	t = 0.1 ms to 10 ms, no voltage reapplied			20 000	kA²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π	$x _{T(AV)} < l < \pi x$	$I_{T(AV)}$), $T_J = T_J$ maximum	0.950	v
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			1.024	v
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum			0.283	
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J maximum$			0.265	mΩ
Maximum on-state voltage drop	V _{TM}	I_{pk} = 3000 A, T _J = 125 °C, t _p = 10 ms sine pulse			1.80	V
Maximum holding current	Ι _Η	T 05 %C	onodo ounalu 1		600	
Typical latching current	١L	$i_{\rm J} = 25^{-1}{\rm G},$	anoue supply 1	2 V resistive load	1000	mA

SWITCHING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum non-repetitive rate of rise of turned-on current	dl/dt	Gate drive 20 V, 20 $\Omega, t_r \leq 1 \; \mu s$ T_J = T_J maximum, anode voltage $\leq 80 \; \% \; V_{DRM}$	1000	A/µs		
Typical delay time	t _d	Gate current 1 A, dl _g /dt = 1 A/ μ s V _d = 0.67 % V _{DRM} , T _J = 25 °C	1.9			
Typical turn-off time	t _q	I_{TM} = 550 A, T_J = T_J maximum, dl/dt = 40 A/µs, V_R = 50 V, dV/dt = 20 V/µs, gate 0 V 100 $\Omega,$ t_p = 500 µs	300	μs		

BLOCKING						
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS		
Maximum critical rate of rise of off-state voltage	dV/dt	$T_J = T_J$ maximum linear to 80 % rated V_{DRM}	500	V/µs		
Maximum peak reverse and off-state leakage current	I _{RRM} , I _{DRM}	$T_J = T_J$ maximum, rated V_{DRM}/V_{RRM} applied	100	mA		



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TRIGGERING						
PABAMETER	SYMBOL			VALUES		UNITS
PARAMETER	STMBUL		ST CONDITIONS	TYP.	MAX.	UNITS
Maximum peak gate power	P_{GM}	$T_J = T_J$ maximum,	$t_p \le 5 \text{ ms}$	1	6	w
Maximum peak average gate power	P _{G(AV)}	$T_J = T_J$ maximum,	f = 50 Hz, d% = 50		3	vv
Maximum peak positive gate current	I _{GM}			3	.0	А
Maximum peak positive gate voltage	+ V _{GM}	$T_J = T_J$ maximum, $t_p \le 5$ ms 20		0	v	
Maximum peak negative gate voltage	- V _{GM}				.0	v
	I _{GT}	$T_J = -40 \ ^\circ C$	Maximum required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode to cathode applied	200	-	
DC gate current required to trigger		$T_J = 25 \ ^\circ C$		100	200	mA
		T _J = 125 °C		50	-	
		$T_J = -40 \ ^\circ C$		1.4	-	
DC gate voltage required to trigger	V _{GT}	T _J = 25 °C		1.1	3.0	V
		T _J = 125 °C		0.9	-	
DC gate current not to trigger	I _{GD}		Maximum gate current/voltage not to trigger is the maximum	1	0	mA
DC gate voltage not to trigger	V _{GD}	$T_J = T_J maximum$	value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.	25	v

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	SYMBOL TEST CONDITIONS		UNITS	
Maximum operating temperature range	TJ		-40 to 125	°C	
Maximum storage temperature range T _S			-40 to 150	C	
Maximum thermal resistance,	D	DC operation single side cooled	0.042		
junction to heatsink	R _{thJ-hs}	DC operation double side cooled	0.021	K/W	
Maximum thermal resistance,		DC operation single side cooled	0.006	r∿ vv	
case to heatsink	R _{thC-hs}	DC operation double side cooled	0.003		
Mounting force, ± 10 %			24 500	Ν	
			(2500)	(kg)	
Approximate weight			425	g	
Case style		See dimensions - link at the end of datasheet	A-24 (K-F	PUK)	

CONDUCTION ANGLE	SINUSOIDAL CONDUCTION		RECTANGULAR CONDUCTION			UNITS
CONDUCTION ANGLE	SINGLE SIDE	DOUBLE SIDE	SINGLE SIDE	DOUBLE SIDE	TEST CONDITIONS	UNITS
180°	0.003	0.003	0.002	0.002	T _J = T _J maximum	
120°	0.004	0.004	0.004	0.004		
90°	0.005	0.005	0.005	0.005		K/W
60°	0.007	0.007	0.007	0.007		
30°	0.012	0.012	0.012	0.012		

Note

• The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

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Fig. 3 - Current Ratings Characteristics

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Fig. 5 - On-State Power Loss Characteristics



Fig. 6 - On-State Power Loss Characteristics

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Fig. 10 - Thermal Impedance Z_{thJ-hs} Characteristics

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ORDERING INFORMATION TABLE

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LINKS TO RELATED DOCUMENTS				
Dimensions	www.vishay.com/doc?95081			



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A-24 (K-PUK)

DIMENSIONS in millimeters (inches)

Creepage distance: 28.88 (1.137) minimum Strike distance: 17.99 (0.708) minimum



Quote between upper and lower pole pieces has to be considered after application of mounting force (see thermal and mechanical specification)



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